

Glass Passivated Ultrafast Rectifier

Major Ratings and Characteristics

$I_{F(AV)}$	5.0 A
V_{RRM}	50 V to 400 V
I_{FSM}	150 A
t_{rr}	50 ns
V_F	0.95 V, 1.25 V
T_j max.	150 °C



*Glass Encapsulation
technique is covered by
Patent No. 3,996,602,
brazed-lead assembly to
Patent No. 3,930,306

Features

- Cavity-free glass-passivated junction
- Ultrafast reverse recovery time
- Low forward voltage drop
- Low leakage current
- Low switching losses, high efficiency
- High forward surge capability
- Solder Dip 260 °C, 40 seconds



Mechanical Data

Case: GP20, molded epoxy over glass body
Epoxy meets UL-94V-0 Flammability rating

Terminals: Matte tin plated leads, solderable per
J-STD-002B and JESD22-B102D
E3 suffix for commercial grade, HE3 suffix for high
reliability grade (AEC Q101 qualified)

Polarity: Color band denotes cathode end

Typical Applications

For use in high frequency rectification and freewheeling application in switching mode converters and inverters for consumer, computer and Telecommunication

Maximum Ratings

$T_A = 25$ °C unless otherwise specified

Parameter	Symbol	EGP50A	EGP50B	EGP50C	EGP50D	EGP50F	EGP50G	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	150	200	300	400	V
Maximum RMS voltage	V_{RMS}	35	70	105	140	210	280	V
Maximum DC blocking voltage	V_{DC}	50	100	150	200	300	400	V
Maximum average forward rectified current 0.375" (9.5 mm) lead length at $T_L = 55$ °C	$I_{F(AV)}$	5						A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	150						A
Operating and storage temperature range	T_J, T_{STG}	- 65 to + 150						°C

EGP50A thru EGP50G



Vishay Semiconductors

Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Test condition	Symbol	EGP50A	EGP50B	EGP50C	EGP50D	EGP50F	EGP50G	Unit
Maximum instantaneous forward voltage	at 5.0 A	V_F		0.95		1.25			V
Maximum DC reverse current at rated DC blocking voltage	$T_A = 25^\circ\text{C}$ $T_A = 125^\circ\text{C}$	I_R		5.0	50				μA
Maximum reverse recovery time	at $I_F = 0.5 \text{ A}$, $I_R = 1.0 \text{ A}$, $I_{rr} = 0.25 \text{ A}$	t_{rr}		50					ns
Typical junction capacitance	at 4.0 V, 1 MHz	C_J		95		75			pF

Thermal Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	EGP50A	EGP50B	EGP50C	EGP50D	EGP50F	EGP50G	Unit
Typical thermal resistance ⁽¹⁾	$R_{\theta JA}$ $R_{\theta JL}$		20	5.0				$^\circ\text{C/W}$

Notes:

(1) Thermal resistance from junction to ambient, and from junction to lead at 0.375" (9.5 mm) lead length, P.C.B. mounted

Ratings and Characteristics Curves

($T_A = 25^\circ\text{C}$ unless otherwise noted)

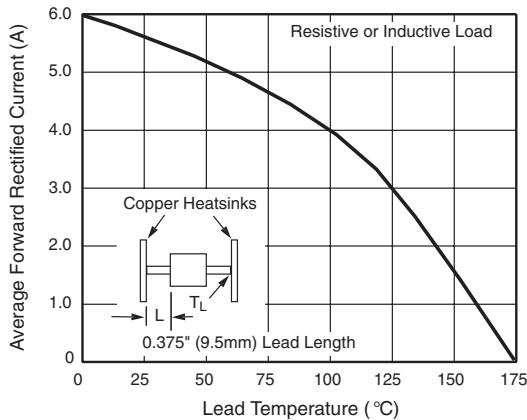


Figure 1. Maximum Forward Current Derating Curve

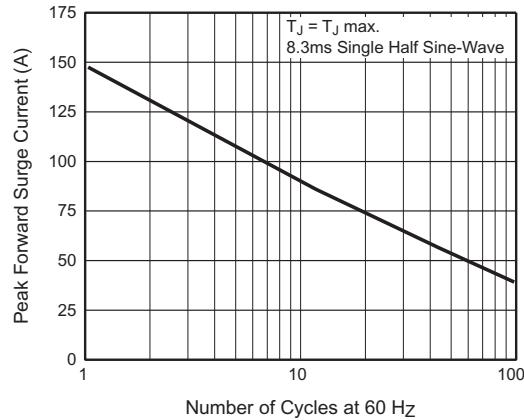


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

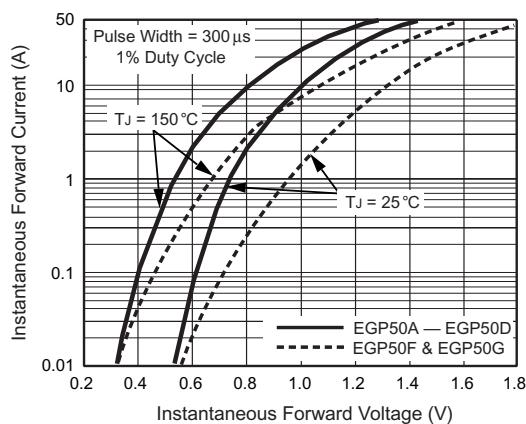


Figure 3. Typical Instantaneous Forward Characteristics

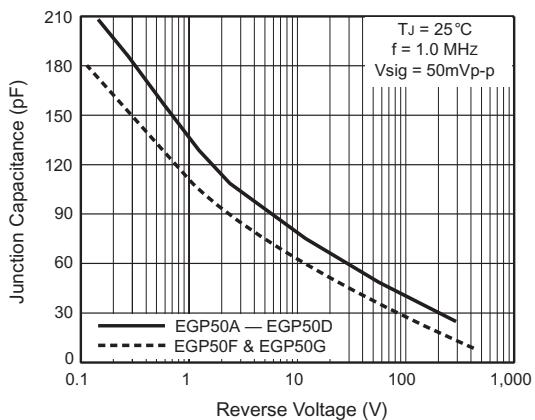


Figure 5. Typical Junction Capacitance

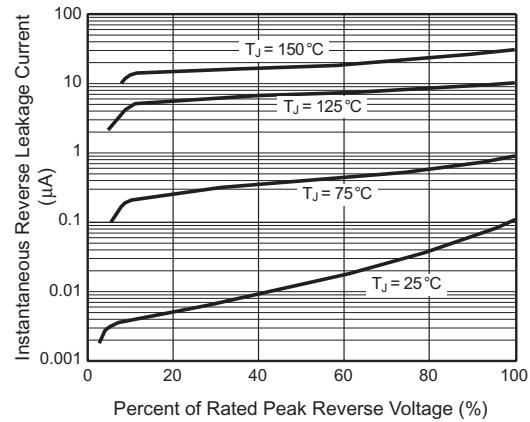


Figure 4. Typical Reverse Leakage Characteristics

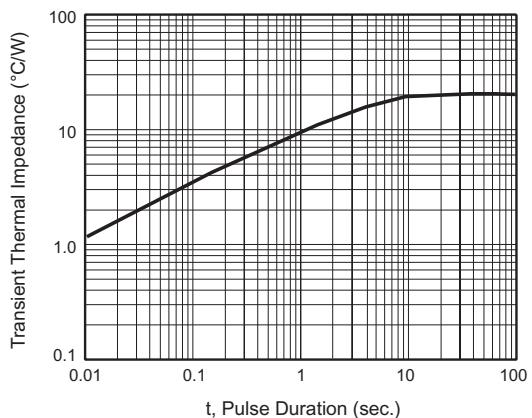


Figure 6. Typical Transient Thermal Impedance

Package outline dimensions in inches (millimeters)

